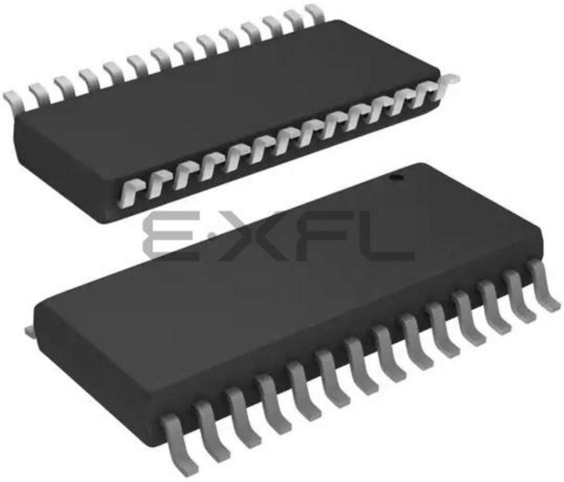
Microchip Technology - PIC16C57CT-20I/SO Datasheet



Details	
Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	20MHz
Connectivity	-
Peripherals	POR, WDT
Number of I/O	20
Program Memory Size	3KB (2K x 12)
Program Memory Type	OTP
EEPROM Size	-
RAM Size	72 x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	-
Oscillator Type	External
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-SOIC (0.295", 7.50mm Width)
Supplier Device Package	28-SOIC
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic16c57ct-20i-so

7.6 I/O Programming Considerations

7.6.1 BI-DIRECTIONAL I/O PORTS

Some instructions operate internally as read followed by write operations. The `BCF` and `BSF` instructions, for example, read the entire port into the CPU, execute the bit operation and re-write the result. Caution must be used when these instructions are applied to a port where one or more pins are used as input/outputs. For example, a `BSF` operation on bit5 of PORTB will cause all eight bits of PORTB to be read into the CPU, bit5 to be set and the PORTB value to be written to the output latches. If another bit of PORTB is used as a bi-directional I/O pin (say bit0) and it is defined as an input at this time, the input signal present on the pin itself would be read into the CPU and rewritten to the data latch of this particular pin, overwriting the previous content. As long as the pin stays in the Input mode, no problem occurs. However, if bit0 is switched into Output mode later on, the content of the data latch may now be unknown.

Example 7-1 shows the effect of two sequential read-modify-write instructions (e.g., `BCF, BSF`, etc.) on an I/O port.

A pin actively outputting a high or a low should not be driven from external devices at the same time in order to change the level on this pin (“wired-or”, “wired-and”). The resulting high output currents may damage the chip.

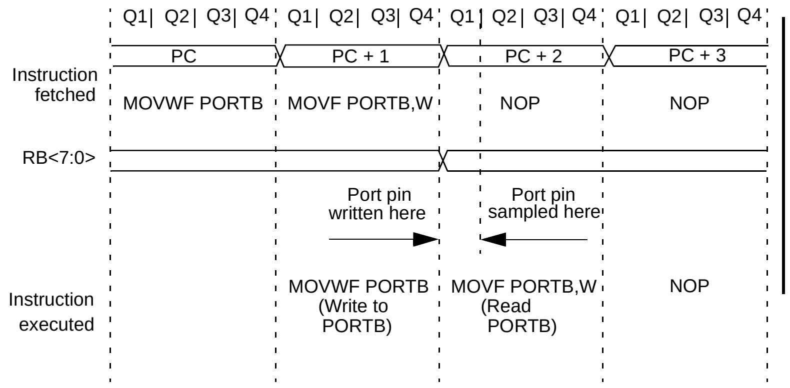
EXAMPLE 7-1: READ-MODIFY-WRITE INSTRUCTIONS ON AN I/O PORT

```
;Initial PORT Settings
; PORTB<7:4> Inputs
; PORTB<3:0> Outputs
;PORTB<7:6> have external pull-ups and are
;not connected to other circuitry
;
;                   PORT latch  PORT pins
;                   ----------  ----------
  BCF   PORTB, 7   ;01pp pppp   11pp pppp
  BCF   PORTB, 6   ;10pp pppp   11pp pppp
  MOVLW H'3F'       ;
  TRIS  PORTB      ;10pp pppp   10pp pppp
;
;Note that the user may have expected the pin
;values to be 00pp pppp. The 2nd BCF caused
;RB7 to be latched as the pin value (High).
```

7.6.2 SUCCESSIVE OPERATIONS ON I/O PORTS

The actual write to an I/O port happens at the end of an instruction cycle, whereas for reading, the data must be valid at the beginning of the instruction cycle (Figure 7-2). Therefore, care must be exercised if a write followed by a read operation is carried out on the same I/O port. The sequence of instructions should allow the pin voltage to stabilize (load dependent) before the next instruction, which causes that file to be read into the CPU, is executed. Otherwise, the previous state of that pin may be read into the CPU rather than the new state. When in doubt, it is better to separate these instructions with a `NOP` or another instruction not accessing this I/O port.

FIGURE 7-2: SUCCESSIVE I/O OPERATION



This example shows a write to PORTB followed by a read from PORTB.

NOTES:

GOTO Unconditional Branch

Syntax:	[*label*] GOTO k
Operands:	0 ≤ k ≤ 511
Operation:	k → PC<8:0>; STATUS<6:5> → PC<10:9>
Status Affected:	None
Encoding:	`101k` | `kkkk` | `kkkk`
Description:	`GOTO` is an unconditional branch. The 9-bit immediate value is loaded into PC bits <8:0>. The upper bits of PC are loaded from STATUS<6:5>. `GOTO` is a two-cycle instruction.
Words:	1
Cycles:	2
Example:	`GOTO THERE`

After Instruction
PC = address (THERE)

INCF Increment f

Syntax:	[*label*] INCF f,d
Operands:	0 ≤ f ≤ 31 d ∈ [0,1]
Operation:	(f) + 1 → (dest)
Status Affected:	Z
Encoding:	`0010` | `10df` | `ffff`
Description:	The contents of register 'f' are incremented. If 'd' is 0 the result is placed in the W register. If 'd' is 1 the result is placed back in register 'f'.
Words:	1
Cycles:	1
Example:	`INCF CNT, 1`

Before Instruction
CNT = 0xFF
Z = 0
After Instruction
CNT = 0x00
Z = 1

INCFSZ Increment f, Skip if 0

Syntax:	[*label*] INCFSZ f,d
Operands:	0 ≤ f ≤ 31 d ∈ [0,1]
Operation:	(f) + 1 → (dest), skip if result = 0
Status Affected:	None
Encoding:	`0011` | `11df` | `ffff`
Description:	The contents of register 'f' are incremented. If 'd' is 0 the result is placed in the W register. If 'd' is 1 the result is placed back in register 'f'. If the result is 0, then the next instruction, which is already fetched, is discarded and a `NOP` is executed instead making it a two-cycle instruction.
Words:	1
Cycles:	1(2)
Example:	

```
HERE      INCFSZ    CNT, 1
          GOTO      LOOP
CONTINUE  •
          •
          •
```

Before Instruction
PC = address (HERE)
After Instruction
CNT = CNT + 1;
if CNT = 0,
PC = address (CONTINUE);
if CNT ≠ 0,
PC = address (HERE +1)

RLF Rotate Left f through Carry

Syntax:	[*label*] RLF f,d
Operands:	$0 \le f \le 31$ $d \in [0,1]$
Operation:	See description below
Status Affected:	C
Encoding:	`0011` `01df` `ffff`
Description:	The contents of register 'f' are rotated one bit to the left through the Carry Flag (STATUS<0>). If 'd' is 0 the result is placed in the W register. If 'd' is 1 the result is stored back in register 'f'. 
Words:	1
Cycles:	1
Example:	`RLF REG1,0`

Before Instruction
REG1 = `1110 0110`
C = `0`
After Instruction
REG1 = `1110 0110`
W = `1100 1100`
C = `1`

RRF Rotate Right f through Carry

Syntax:	[*label*] RRF f,d
Operands:	$0 \le f \le 31$ $d \in [0,1]$
Operation:	See description below
Status Affected:	C
Encoding:	`0011` `00df` `ffff`
Description:	The contents of register 'f' are rotated one bit to the right through the Carry Flag (STATUS<0>). If 'd' is 0 the result is placed in the W register. If 'd' is 1 the result is placed back in register 'f'. 
Words:	1
Cycles:	1
Example:	`RRF REG1,0`

Before Instruction
REG1 = `1110 0110`
C = `0`
After Instruction
REG1 = `1110 0110`
W = `0111 0011`
C = `0`

SLEEP Enter SLEEP Mode

Syntax:	[*label*] SLEEP
Operands:	None
Operation:	00h → WDT; 0 → WDT prescaler; if assigned 1 → $\overline{TO}$; 0 → $\overline{PD}$
Status Affected:	$\overline{TO}$, $\overline{PD}$
Encoding:	`0000` `0000` `0011`
Description:	Time-out status bit ($\overline{TO}$) is set. The power-down status bit ($\overline{PD}$) is cleared. The WDT and its prescaler are cleared. The processor is put into SLEEP mode with the oscillator stopped. See section on SLEEP for more details.
Words:	1
Cycles:	1
Example:	`SLEEP`

12.2 DC Characteristics: PIC16C54/55/56/57-RCI, XTI, 10I, HSI, LPI (Industrial)

PIC16C54/55/56/57-RCI, XTI, 10I, HSI, LPI (Industrial)			**Standard Operating Conditions (unless otherwise specified)** Operating Temperature –40°C ≤ TA ≤ +85°C for industrial				
Param No.	**Symbol**	**Characteristic/Device**	**Min**	**Typ†**	**Max**	**Units**	**Conditions**
D001	VDD	**Supply Voltage**					
		PIC16C5X-RCI	3.0	—	6.25	V	
		PIC16C5X-XTI	3.0	—	6.25	V	
		PIC16C5X-10I	4.5	—	5.5	V	
		PIC16C5X-HSI	4.5	—	5.5	V	
		PIC16C5X-LPI	2.5	—	6.25	V	
D002	VDR	**RAM Data Retention Voltage**(1)	—	1.5*	—	V	Device in SLEEP mode
D003	VPOR	**VDD Start Voltage** to ensure Power-on Reset	—	VSS	—	V	See Section 5.1 for details on Power-on Reset
D004	SVDD	**VDD Rise Rate** to ensure Power-on Reset	0.05*	—	—	V/ms	See Section 5.1 for details on Power-on Reset
D010	IDD	**Supply Current**(2)					
		PIC16C5X-RCI(3)	—	1.8	3.3	mA	FOSC = 4 MHz, VDD = 5.5V
		PIC16C5X-XTI	—	1.8	3.3	mA	FOSC = 4 MHz, VDD = 5.5V
		PIC16C5X-10I	—	4.8	10	mA	FOSC = 10 MHz, VDD = 5.5V
		PIC16C5X-HSI	—	4.8	10	mA	FOSC = 10 MHz, VDD = 5.5V
		PIC16C5X-HSI	—	9.0	20	mA	FOSC = 20 MHz, VDD = 5.5V
		PIC16C5X-LPI	—	15	40	μA	FOSC = 32 kHz, VDD = 3.0V, WDT disabled
D020	IPD	**Power-down Current**(2)	—	4.0	14	μA	VDD = 3.0V, WDT enabled
			—	0.6	12	μA	VDD = 3.0V, WDT disabled

* These parameters are characterized but not tested.

† Data in “Typ” column is based on characterization results at 25°C. This data is for design guidance only and is not tested.

Note 1: This is the limit to which VDD can be lowered in SLEEP mode without losing RAM data.

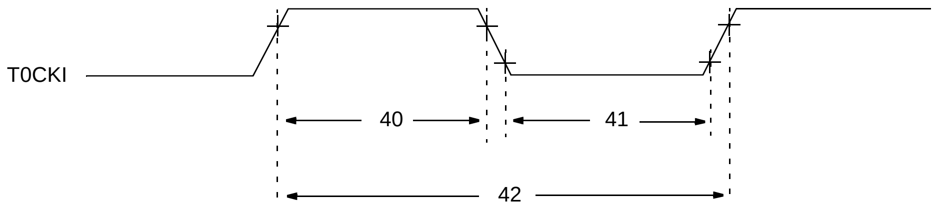
2: The supply current is mainly a function of the operating voltage and frequency. Other factors such as bus loading, oscillator type, bus rate, internal code execution pattern and temperature also have an impact on the current consumption.

a) The test conditions for all IDD measurements in active Operation mode are: OSC1 = external square wave, from rail-to-rail; all I/O pins tristated, pulled to VSS, T0CKI = VDD, $\overline{\text{MCLR}}$ = VDD; WDT enabled/disabled as specified.

b) For standby current measurements, the conditions are the same, except that the device is in SLEEP mode. The power-down current in SLEEP mode does not depend on the oscillator type.

3: Does not include current through REXT. The current through the resistor can be estimated by the formula: IR = VDD/2REXT (mA) with REXT in kΩ.

FIGURE 12-5: TIMER0 CLOCK TIMINGS - PIC16C54/55/56/57



Note: Please refer to Figure 12-1 for load conditions.

TABLE 12-4: TIMER0 CLOCK REQUIREMENTS - PIC16C54/55/56/57

AC Characteristics	**Standard Operating Conditions (unless otherwise specified)** Operating Temperature 0°C ≤ T_A ≤ +70°C for commercial –40°C ≤ T_A ≤ +85°C for industrial –40°C ≤ T_A ≤ +125°C for extended						
Param No.	**Symbol**	**Characteristic**	**Min**	**Typ†**	**Max**	**Units**	**Conditions**
40	Tt0H	T0CKI High Pulse Width - No Prescaler	0.5 T_{CY} + 20*	—	—	ns	
		- With Prescaler	10*	—	—	ns	
41	Tt0L	T0CKI Low Pulse Width - No Prescaler	0.5 T_{CY} + 20*	—	—	ns	
		- With Prescaler	10*	—	—	ns	
42	Tt0P	T0CKI Period	20 or $\frac{T_{CY} + 40}{N}$*	—	—	ns	Whichever is greater. N = Prescale Value (1, 2, 4,..., 256)

* These parameters are characterized but not tested.

† Data in the Typical ("Typ") column is at 5.0V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

FIGURE 14-2: TYPICAL RC OSC FREQUENCY vs. VDD, CEXT = 20 PF

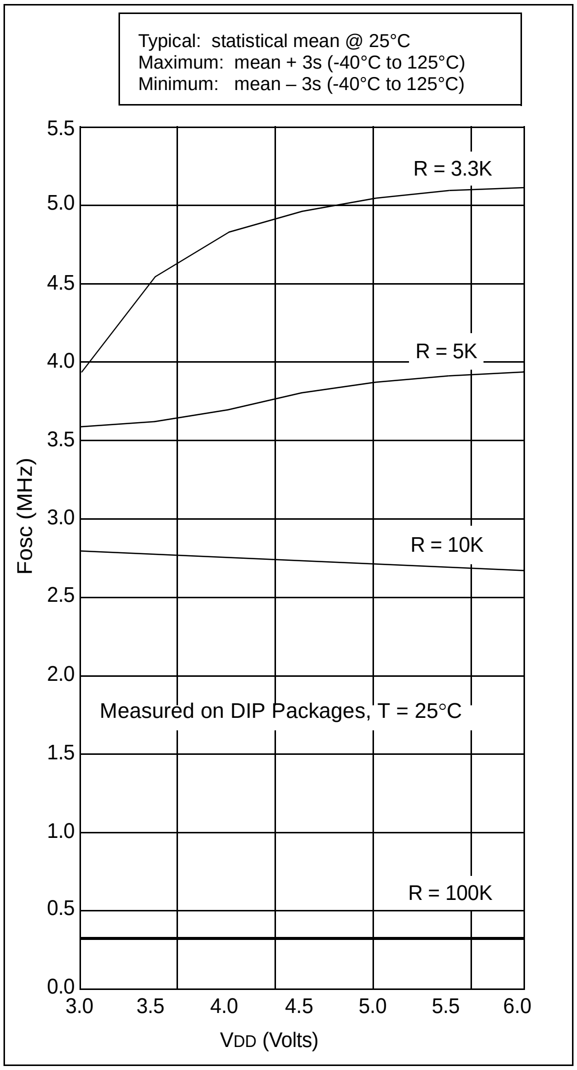


FIGURE 14-3: TYPICAL RC OSC FREQUENCY vs. VDD, CEXT = 100 PF

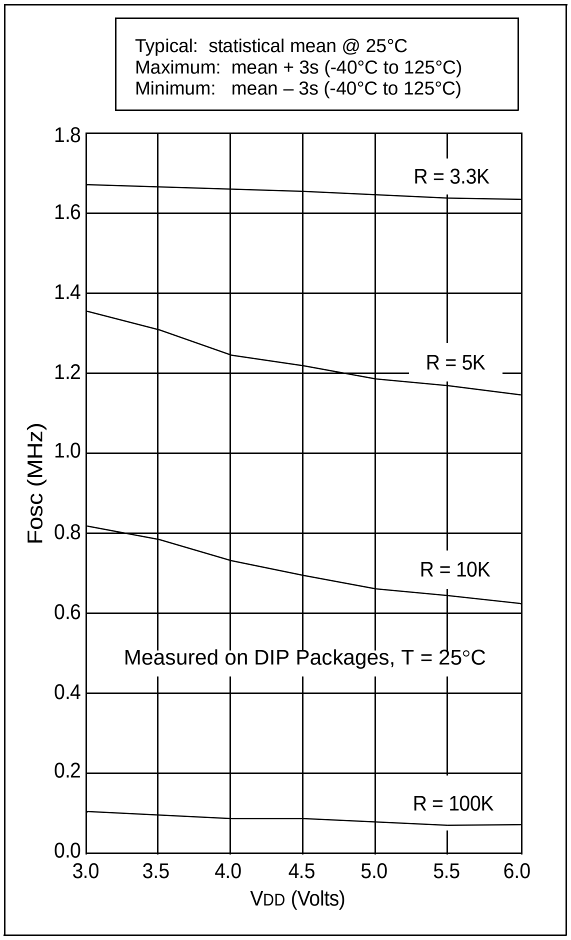


FIGURE 14-4: TYPICAL RC OSC FREQUENCY vs. VDD, CEXT = 300 PF

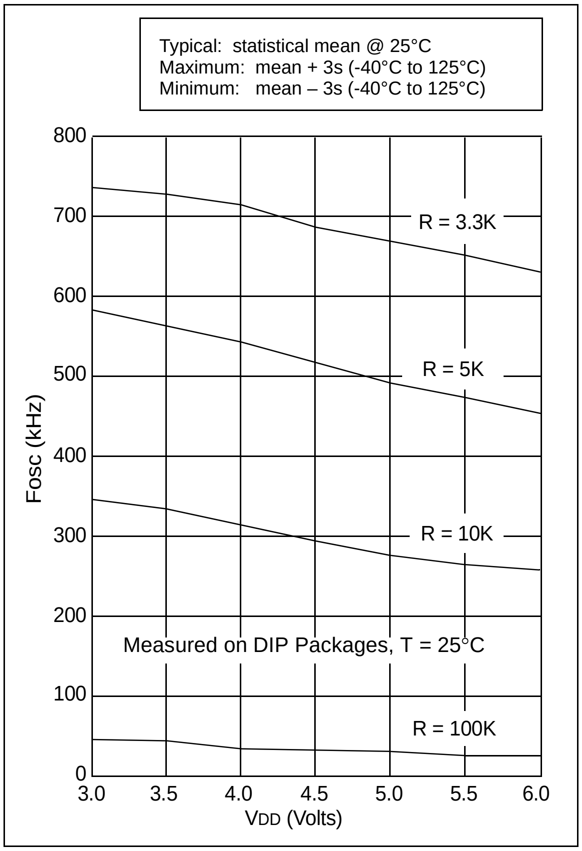
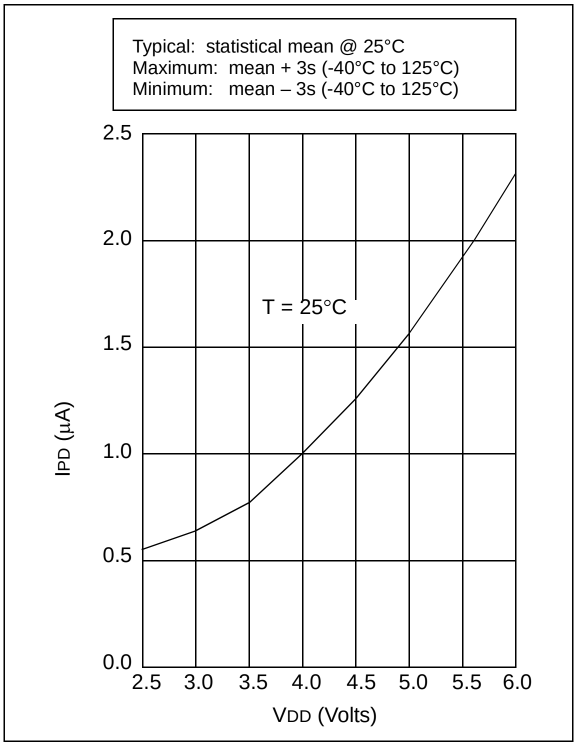


FIGURE 14-5: TYPICAL IPD vs. VDD, WATCHDOG DISABLED



15.2 DC Characteristics: PIC16C54A-04E, 10E, 20E (Extended) PIC16LC54A-04E (Extended)

PIC16LC54A-04E (Extended)	**Standard Operating Conditions (unless otherwise specified)** Operating Temperature –40°C ≤ TA ≤ +125°C for extended
PIC16C54A-04E, 10E, 20E (Extended)	**Standard Operating Conditions (unless otherwise specified)** Operating Temperature –40°C ≤ TA ≤ +125°C for extended

Param No.	Symbol	Characteristic	Min	Typ†	Max	Units	Conditions
D001	VDD	**Supply Voltage**					
		PIC16LC54A	3.0 2.5	— —	6.25 6.25	V V	XT and RC modes LP mode
D001A		PIC16C54A	3.5 4.5	— —	5.5 5.5	V V	RC and XT modes HS mode
D002	VDR	**RAM Data Retention Voltage(1)**	—	1.5*	—	V	Device in SLEEP mode
D003	VPOR	**VDD Start Voltage** to ensure Power-on Reset	—	Vss	—	V	See Section 5.1 for details on Power-on Reset
D004	SVDD	**VDD Rise Rate** to ensure Power-on Reset	0.05*	—	—	V/ms	See Section 5.1 for details on Power-on Reset
D010	IDD	**Supply Current(2)**					
		PIC16LC54A	—	0.5	25	mA	FOSC = 4.0 MHz, VDD = 5.5V, RC(3) and XT modes
			—	11	27	μA	FOSC = 32 kHz, VDD = 2.5V, LP mode, Commercial
			—	11	35	μA	FOSC = 32 kHz, VDD = 2.5V, LP mode, Industrial
			—	11	37	μA	FOSC = 32 kHz, VDD = 2.5V, LP mode, Extended
D010A		PIC16C54A	—	1.8	3.3	mA	FOSC = 4.0 MHz, VDD = 5.5V, RC(3) and XT modes
			—	4.8	10	mA	FOSC = 10 MHz, VDD = 5.5V, HS mode
			—	9.0	20	mA	FOSC = 20 MHz, VDD = 5.5V, HS mode

Legend: Rows with standard voltage device data only are shaded for improved readability.

* These parameters are characterized but not tested.

† Data in the Typical (“Typ”) column is based on characterization results at 25°C. This data is for design guidance only and is not tested.

Note 1: This is the limit to which VDD can be lowered in SLEEP mode without losing RAM data.

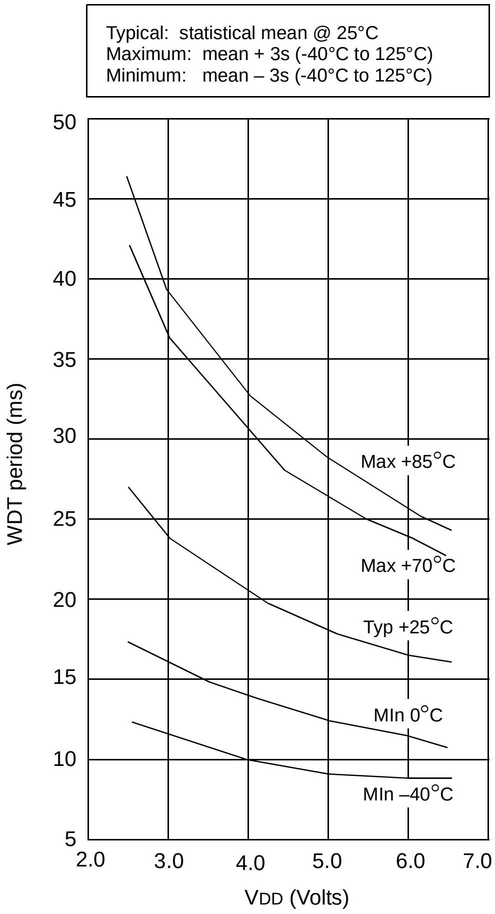
2: The supply current is mainly a function of the operating voltage and frequency. Other factors such as bus loading, oscillator type, bus rate, internal code execution pattern and temperature also have an impact on the current consumption.

a) The test conditions for all IDD measurements in active Operation mode are: OSC1 = external square wave, from rail-to-rail; all I/O pins tristated, pulled to VSS, T0CKI = VDD, $\overline{\text{MCLR}}$ = VDD; WDT enabled/disabled as specified.

b) For standby current measurements, the conditions are the same, except that the device is in SLEEP mode. The power-down current in SLEEP mode does not depend on the oscillator type.

3: Does not include current through REXT. The current through the resistor can be estimated by the formula: IR = VDD/2REXT (mA) with REXT in kΩ.

FIGURE 16-16: WDT TIMER TIME-OUT PERIOD vs. VDD[1]



Note 1: Prescaler set to 1:1.

FIGURE 16-17: TRANSCONDUCTANCE (gm) OF HS OSCILLATOR vs. VDD

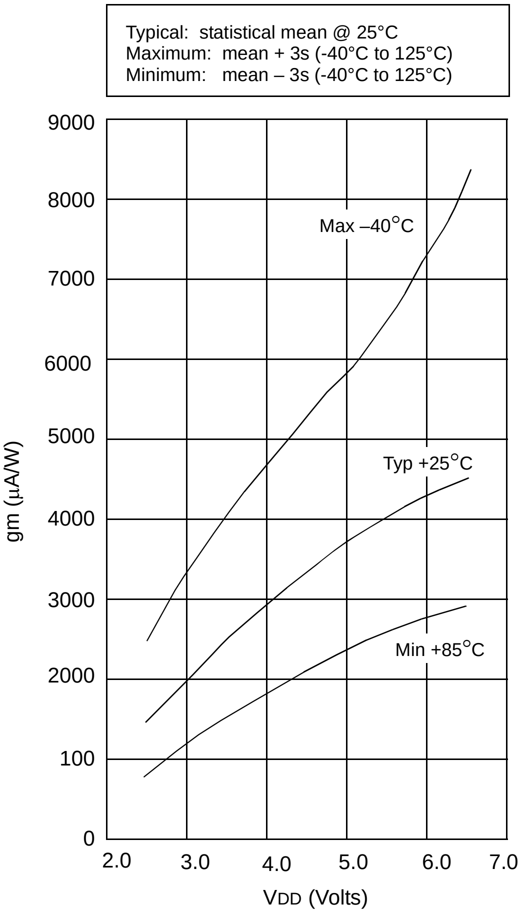


FIGURE 16-18: TRANSCONDUCTANCE (gm) OF LP OSCILLATOR vs. VDD

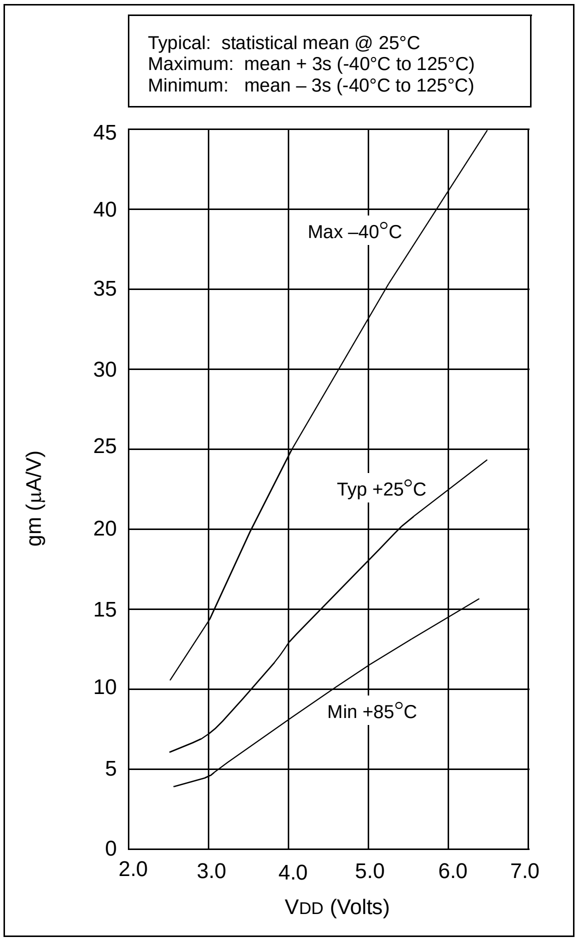


FIGURE 16-19: TRANSCONDUCTANCE (gm) OF XT OSCILLATOR vs. VDD

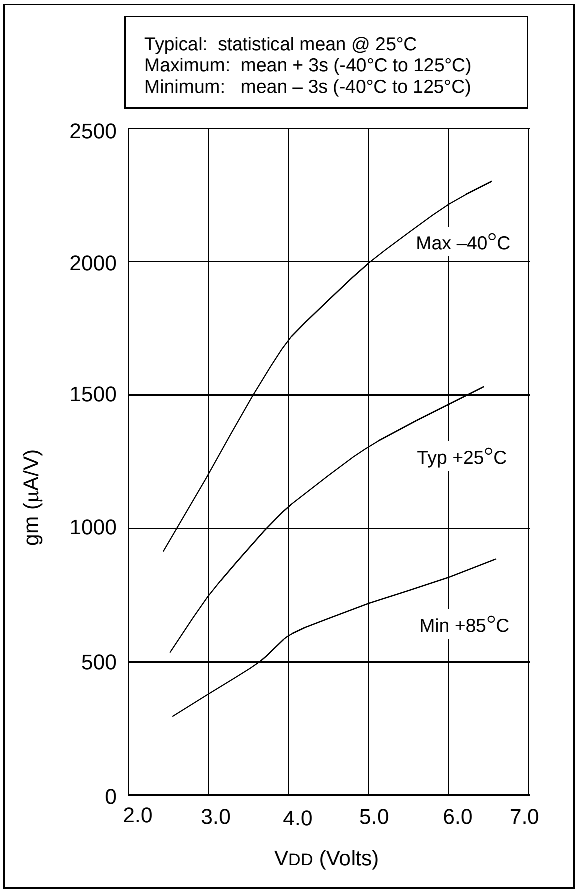


FIGURE 16-22: PORTA, B AND C I_{OL} VS. V_{OL}, V_{DD} = 3V

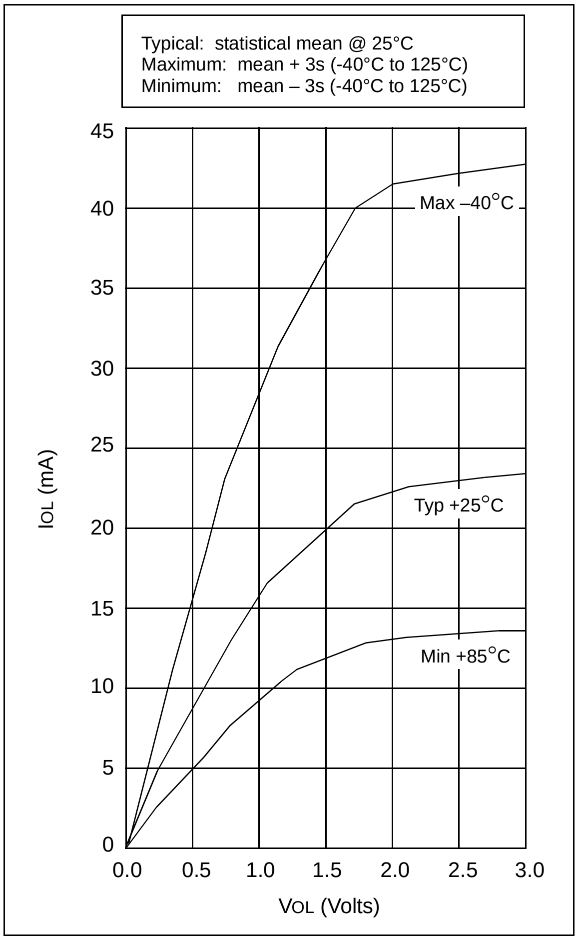


FIGURE 16-23: PORTA, B AND C I_{OL} VS. V_{OL}, V_{DD} = 5V

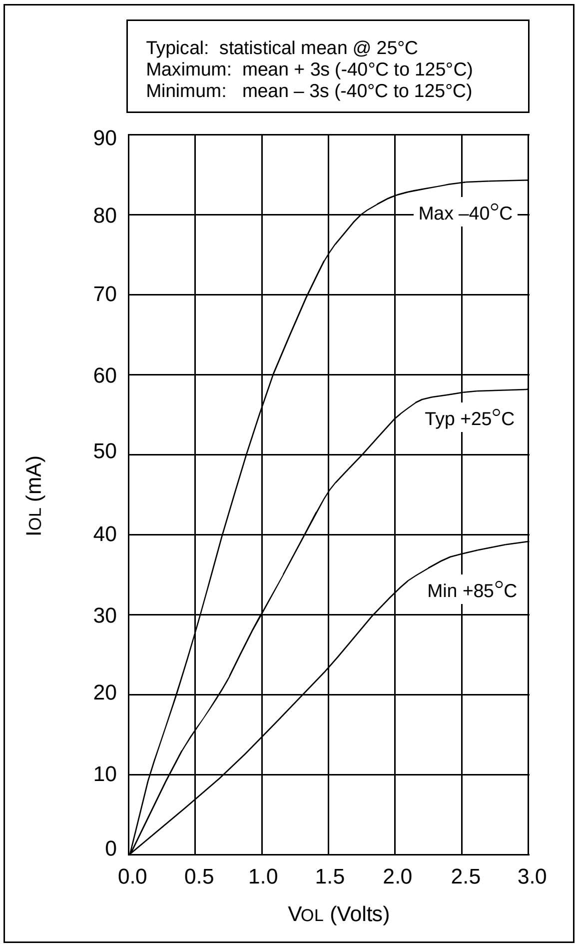


TABLE 16-2: INPUT CAPACITANCE FOR PIC16C54A/C58A

Pin	Typical Capacitance (pF)	
	18L PDIP	18L SOIC
RA port	5.0	4.3
RB port	5.0	4.3
$\overline{\text{MCLR}}$	17.0	17.0
OSC1	4.0	3.5
OSC2/CLKOUT	4.3	3.5
T0CKI	3.2	2.8

All capacitance values are typical at 25°C. A part-to-part variation of ±25% (three standard deviations) should be taken into account.

17.1 DC Characteristics: PIC16C54C/C55A/C56A/C57C/C58B-04, 20 (Commercial, Industrial)
PIC16LC54C/LC55A/LC56A/LC57C/LC58B-04 (Commercial, Industrial)
PIC16CR54C/CR56A/CR57C/CR58B-04, 20 (Commercial, Industrial)
PIC16LCR54C/LCR56A/LCR57C/LCR58B-04 (Commercial, Industrial)

<table>
<tr><td colspan="3">PIC16LC5X
PIC16LCR5X
(Commercial, Industrial)</td><td colspan="5">Standard Operating Conditions (unless otherwise specified)
Operating Temperature 0°C ≤ TA ≤ +70°C for commercial
–40°C ≤ TA ≤ +85°C for industrial</td></tr>
<tr><td colspan="3">PIC16C5X
PIC16CR5X
(Commercial, Industrial)</td><td colspan="5">Standard Operating Conditions (unless otherwise specified)
Operating Temperature 0°C ≤ TA ≤ +70°C for commercial
–40°C ≤ TA ≤ +85°C for industrial</td></tr>
<tr><th>Param No.</th><th>Symbol</th><th>Characteristic/Device</th><th>Min</th><th>Typ†</th><th>Max</th><th>Units</th><th>Conditions</th></tr>
<tr><td></td><td>IDD</td><td colspan="6">Supply Current(2,3)</td></tr>
<tr><td>D010</td><td></td><td>PIC16LC5X</td><td>—</td><td>0.5</td><td>2.4</td><td>mA</td><td>FOSC = 4.0 MHz, VDD = 5.5V, XT and RC modes</td></tr>
<tr><td></td><td></td><td></td><td>—</td><td>11</td><td>27</td><td>μA</td><td>FOSC = 32 kHz, VDD = 2.5V, LP mode, Commercial</td></tr>
<tr><td></td><td></td><td></td><td>—</td><td>14</td><td>35</td><td>μA</td><td>FOSC = 32 kHz, VDD = 2.5V, LP mode, Industrial</td></tr>
<tr><td>D010A</td><td></td><td>PIC16C5X</td><td>—</td><td>1.8</td><td>2.4</td><td>mA</td><td>FOSC = 4 MHz, VDD = 5.5V, XT and RC modes</td></tr>
<tr><td></td><td></td><td></td><td>—</td><td>2.6</td><td>3.6*</td><td>mA</td><td>FOSC = 10 MHz, VDD = 3.0V, HS mode</td></tr>
<tr><td></td><td></td><td></td><td>—</td><td>4.5</td><td>16</td><td>mA</td><td>FOSC = 20 MHz, VDD = 5.5V, HS mode</td></tr>
<tr><td></td><td></td><td></td><td>—</td><td>14</td><td>32</td><td>μA</td><td>FOSC = 32 kHz, VDD = 3.0V, LP mode, Commercial</td></tr>
<tr><td></td><td></td><td></td><td>—</td><td>17</td><td>40</td><td>μA</td><td>FOSC = 32 kHz, VDD = 3.0V, LP mode, Industrial</td></tr>
</table>

Legend: Rows with standard voltage device data only are shaded for improved readability.

* These parameters are characterized but not tested.

† Data in “Typ” column is at 5V, 25°C, unless otherwise stated. These parameters are for design guidance only, and are not tested.

Note 1: This is the limit to which VDD can be lowered in SLEEP mode without losing RAM data.

2: The supply current is mainly a function of the operating voltage and frequency. Other factors such as bus loading, oscillator type, bus rate, internal code execution pattern and temperature also have an impact on the current consumption.

a) The test conditions for all IDD measurements in active Operation mode are: OSC1 = external square wave, from rail-to-rail; all I/O pins tristated, pulled to VSS, T0CKI = VDD, $\overline{MCLR}$ = VDD; WDT enabled/disabled as specified.

b) For standby current measurements, the conditions are the same, except that the device is in SLEEP mode. The power-down current in SLEEP mode does not depend on the oscillator type.

3: Does not include current through REXT. The current through the resistor can be estimated by the formula:
IR = VDD/2REXT (mA) with REXT in kΩ.

17.4 Timing Parameter Symbology and Load Conditions

The timing parameter symbols have been created with one of the following formats:

1. TppS2ppS
2. TppS

T			
F	Frequency	T	Time

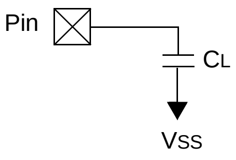
Lowercase letters (pp) and their meanings:

pp			
2	to	mc	$\overline{\text{MCLR}}$
ck	CLKOUT	osc	oscillator
cy	cycle time	os	OSC1
drt	device reset timer	t0	T0CKI
io	I/O port	wdt	watchdog timer

Uppercase letters and their meanings:

S			
F	Fall	P	Period
H	High	R	Rise
I	Invalid (Hi-impedance)	V	Valid
L	Low	Z	Hi-impedance

FIGURE 17-5: LOAD CONDITIONS FOR DEVICE TIMING SPECIFICATIONS - PIC16C54C/CR54C/C55A/C56A/CR56A/C57C/CR57C/C58B/CR58B-04, 20



C_L = 50 pF for all pins and OSC2 for RC mode

0 -15 pF for OSC2 in XT, HS or LP modes when external clock is used to drive OSC1

17.5 Timing Diagrams and Specifications

FIGURE 17-6: EXTERNAL CLOCK TIMING - PIC16C5X, PIC16CR5X

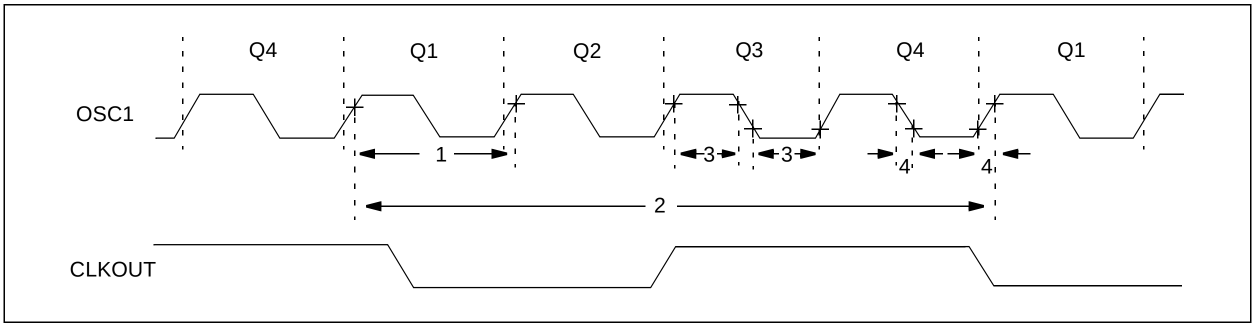


TABLE 17-1: EXTERNAL CLOCK TIMING REQUIREMENTS - PIC16C5X, PIC16CR5X

AC Characteristics	**Standard Operating Conditions (unless otherwise specified)** Operating Temperature 0°C ≤ T_A ≤ +70°C for commercial –40°C ≤ T_A ≤ +85°C for industrial –40°C ≤ T_A ≤ +125°C for extended

Param No.	Symbol	Characteristic	Min	Typ†	Max	Units	Conditions
	FOSC	External CLKIN Frequency(1)	DC	—	4.0	MHz	XT OSC mode
			DC	—	4.0	MHz	HS OSC mode (04)
			DC	—	20	MHz	HS OSC mode (20)
			DC	—	200	kHz	LP OSC mode
		Oscillator Frequency(1)	DC	—	4.0	MHz	RC OSC mode
			0.45	—	4.0	MHz	XT OSC mode
			4.0	—	4.0	MHz	HS OSC mode (04)
			4.0	—	20	MHz	HS OSC mode (20)
			5.0	—	200	kHz	LP OSC mode
1	TOSC	External CLKIN Period(1)	250	—	—	ns	XT OSC mode
			250	—	—	ns	HS OSC mode (04)
			50	—	—	ns	HS OSC mode (20)
			5.0	—	—	µs	LP OSC mode
		Oscillator Period(1)	250	—	—	ns	RC OSC mode
			250	—	2,200	ns	XT OSC mode
			250	—	250	ns	HS OSC mode (04)
			50	—	250	ns	HS OSC mode (20)
			5.0	—	200	µs	LP OSC mode

* These parameters are characterized but not tested.

† Data in the Typical (“Typ”) column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: All specified values are based on characterization data for that particular oscillator type under standard operating conditions with the device executing code. Exceeding these specified limits may result in an unstable oscillator operation and/or higher than expected current consumption.
When an external clock input is used, the “max” cycle time limit is “DC” (no clock) for all devices.

2: Instruction cycle period (TCY) equals four times the input oscillator time base period.

FIGURE 18-16: PORTA, B AND C I_{OH} vs. V_{OH}, V_{DD} = 5 V

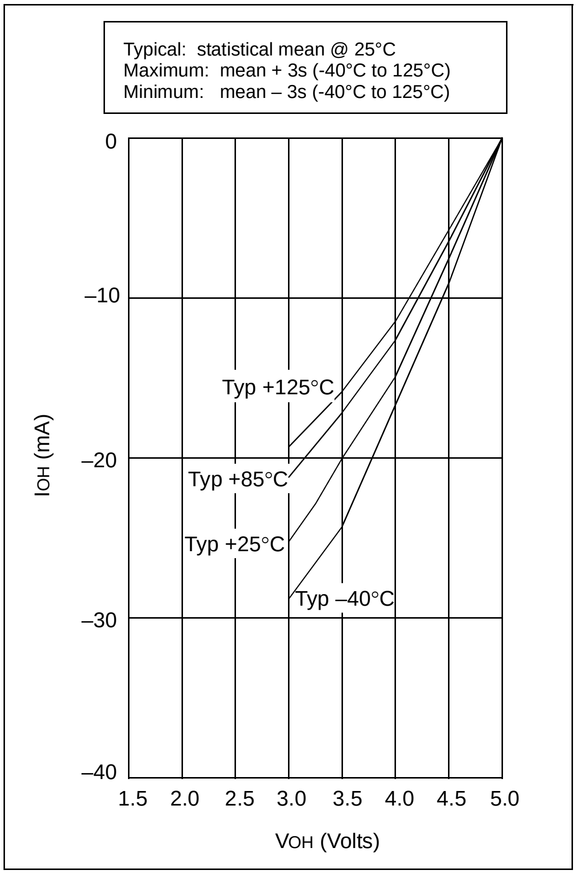
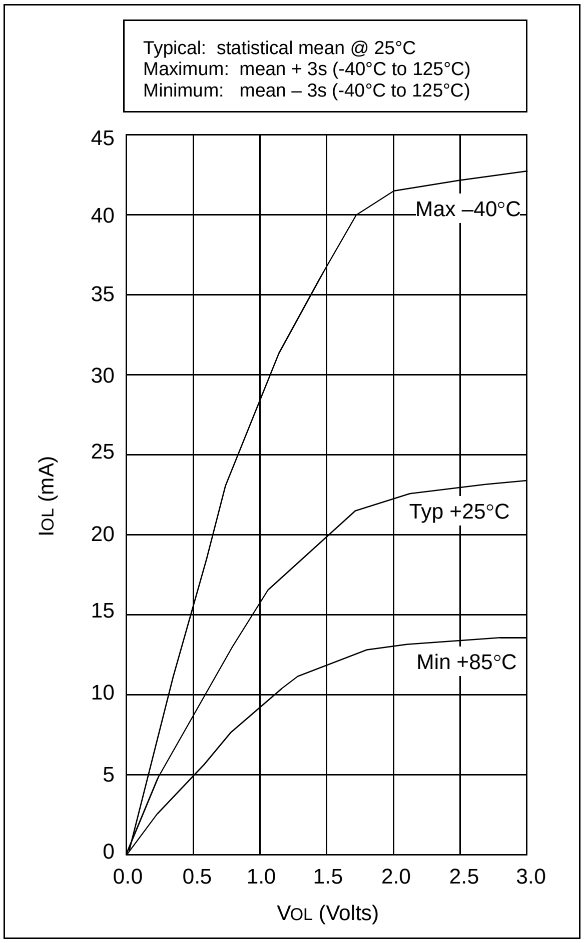
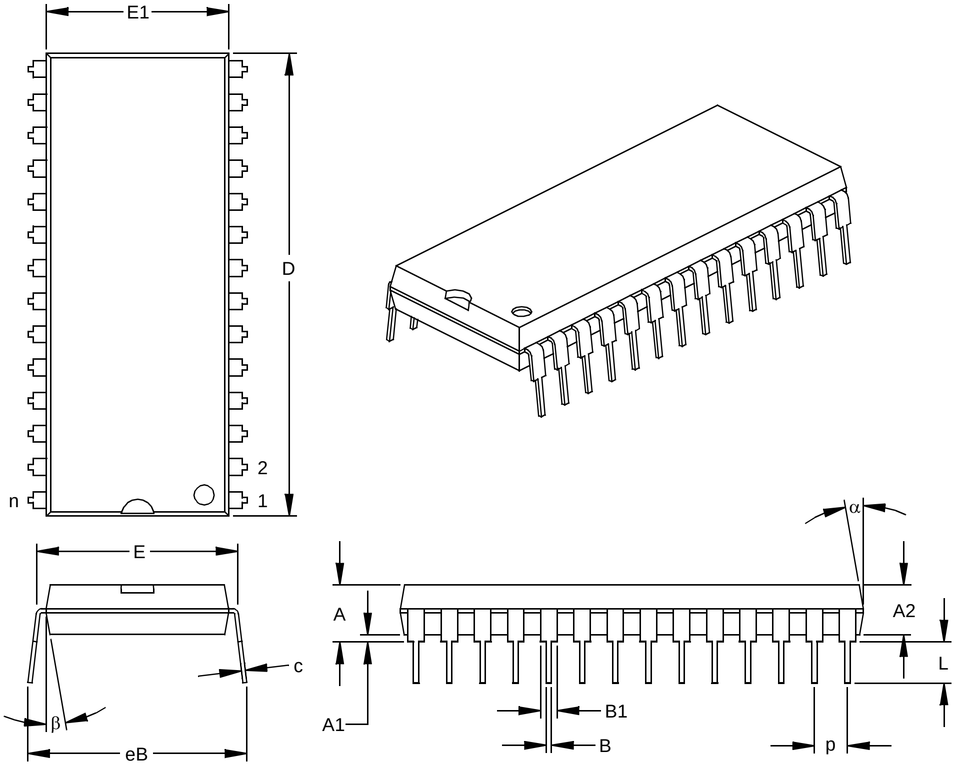


FIGURE 18-17: PORTA, B AND C I_{OL} vs. V_{OL}, V_{DD} = 3 V



28-Lead Plastic Dual In-line (P) – 600 mil (PDIP)

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



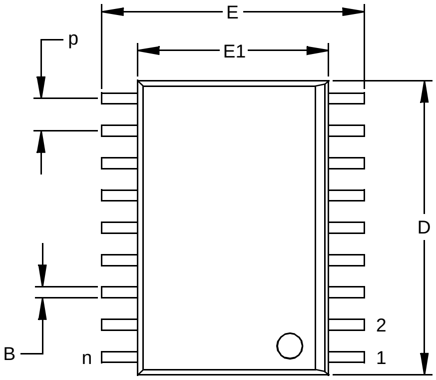
Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		28			28	
Pitch	p		.100			2.54	
Top to Seating Plane	A	.160	.175	.190	4.06	4.45	4.83
Molded Package Thickness	A2	.140	.150	.160	3.56	3.81	4.06
Base to Seating Plane	A1	.015			0.38		
Shoulder to Shoulder Width	E	.595	.600	.625	15.11	15.24	15.88
Molded Package Width	E1	.505	.545	.560	12.83	13.84	14.22
Overall Length	D	1.395	1.430	1.465	35.43	36.32	37.21
Tip to Seating Plane	L	.120	.130	.135	3.05	3.30	3.43
Lead Thickness	c	.008	.012	.015	0.20	0.29	0.38
Upper Lead Width	B1	.030	.050	.070	0.76	1.27	1.78
Lower Lead Width	B	.014	.018	.022	0.36	0.46	0.56
Overall Row Spacing §	eB	.620	.650	.680	15.75	16.51	17.27
Mold Draft Angle Top	α	5	10	15	5	10	15
Mold Draft Angle Bottom	β	5	10	15	5	10	15

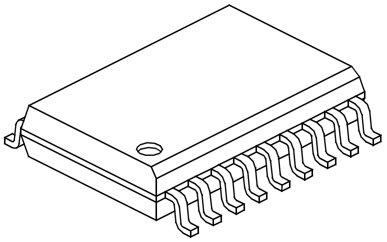
* Controlling Parameter
§ Significant Characteristic

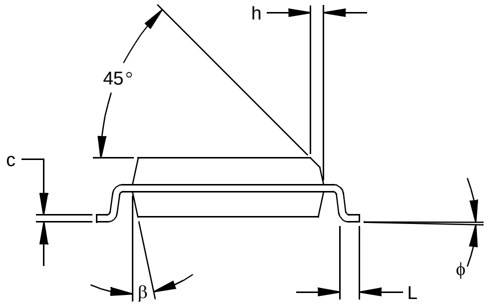
Notes:
Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010” (0.254mm) per side.
JEDEC Equivalent: MO-011
Drawing No. C04-079

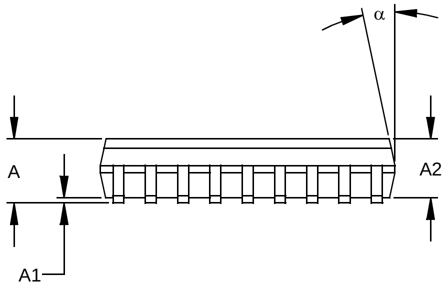
18-Lead Plastic Small Outline (SO) – Wide, 300 mil (SOIC)

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging









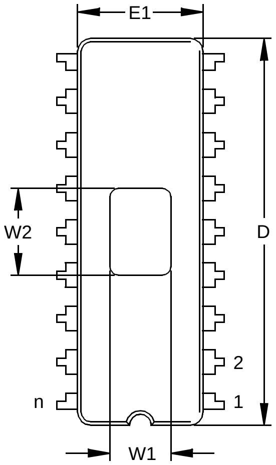
Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		18			18	
Pitch	p		.050			1.27	
Overall Height	A	.093	.099	.104	2.36	2.50	2.64
Molded Package Thickness	A2	.088	.091	.094	2.24	2.31	2.39
Standoff §	A1	.004	.008	.012	0.10	0.20	0.30
Overall Width	E	.394	.407	.420	10.01	10.34	10.67
Molded Package Width	E1	.291	.295	.299	7.39	7.49	7.59
Overall Length	D	.446	.454	.462	11.33	11.53	11.73
Chamfer Distance	h	.010	.020	.029	0.25	0.50	0.74
Foot Length	L	.016	.033	.050	0.41	0.84	1.27
Foot Angle	φ	0	4	8	0	4	8
Lead Thickness	c	.009	.011	.012	0.23	0.27	0.30
Lead Width	B	.014	.017	.020	0.36	0.42	0.51
Mold Draft Angle Top	α	0	12	15	0	12	15
Mold Draft Angle Bottom	β	0	12	15	0	12	15

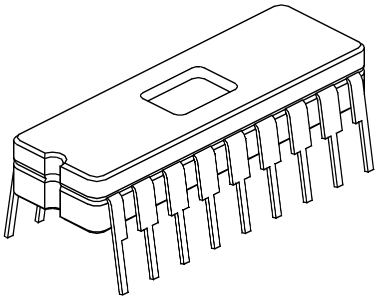
* Controlling Parameter
§ Significant Characteristic

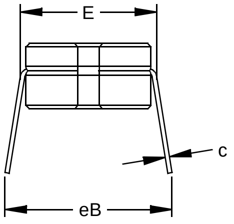
Notes:
Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010” (0.254mm) per side.
JEDEC Equivalent: MS-013
Drawing No. C04-051

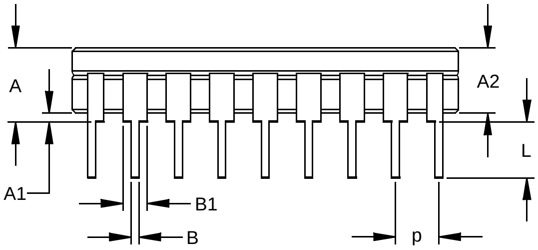
18-Lead Ceramic Dual In-line with Window (JW) – 300 mil (CERDIP)

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging







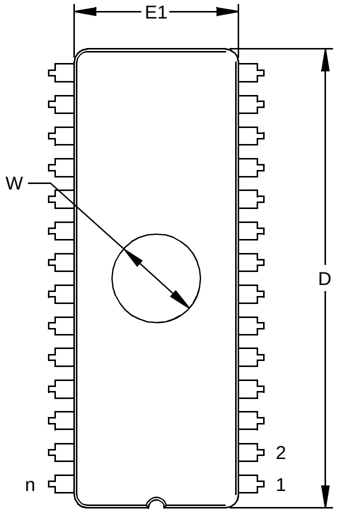


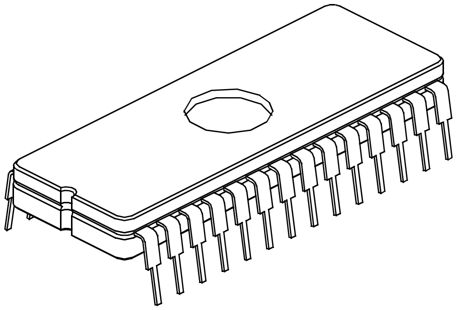
Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		18			18	
Pitch	p		.100			2.54	
Top to Seating Plane	A	.170	.183	.195	4.32	4.64	4.95
Ceramic Package Height	A2	.155	.160	.165	3.94	4.06	4.19
Standoff	A1	.015	.023	.030	0.38	0.57	0.76
Shoulder to Shoulder Width	E	.300	.313	.325	7.62	7.94	8.26
Ceramic Pkg. Width	E1	.285	.290	.295	7.24	7.37	7.49
Overall Length	D	.880	.900	.920	22.35	22.86	23.37
Tip to Seating Plane	L	.125	.138	.150	3.18	3.49	3.81
Lead Thickness	c	.008	.010	.012	0.20	0.25	0.30
Upper Lead Width	B1	.050	.055	.060	1.27	1.40	1.52
Lower Lead Width	B	.016	.019	.021	0.41	0.47	0.53
Overall Row Spacing §	eB	.345	.385	.425	8.76	9.78	10.80
Window Width	W1	.130	.140	.150	3.30	3.56	3.81
Window Length	W2	.190	.200	.210	4.83	5.08	5.33

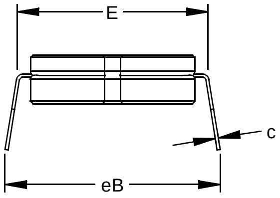
* Controlling Parameter
§ Significant Characteristic
JEDEC Equivalent: MO-036
Drawing No. C04-010

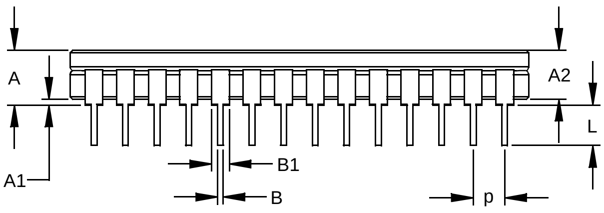
28-Lead Ceramic Dual In-line with Window (JW) – 600 mil (CERDIP)

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging









Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		28			28	
Pitch	p		.100			2.54	
Top to Seating Plane	A	.195	.210	.225	4.95	5.33	5.72
Ceramic Package Height	A2	.155	.160	.165	3.94	4.06	4.19
Standoff	A1	.015	.038	.060	0.38	0.95	1.52
Shoulder to Shoulder Width	E	.595	.600	.625	15.11	15.24	15.88
Ceramic Pkg. Width	E1	.514	.520	.526	13.06	13.21	13.36
Overall Length	D	1.430	1.460	1.490	36.32	37.08	37.85
Tip to Seating Plane	L	.125	.138	.150	3.18	3.49	3.81
Lead Thickness	c	.008	.010	.012	0.20	0.25	0.30
Upper Lead Width	B1	.050	.058	.065	1.27	1.46	1.65
Lower Lead Width	B	.016	.020	.023	0.41	0.51	0.58
Overall Row Spacing §	eB	.610	.660	.710	15.49	16.76	18.03
Window Diameter	W	.270	.280	.290	6.86	7.11	7.37

* Controlling Parameter
§ Significant Characteristic
JEDEC Equivalent: MO-103
Drawing No. C04-013